

PATENT APPLICATION

Sheet 1 of 9

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
	200315134-1	10/799,325	
	APPLICANT		
	Randy L. Hoffman		
	FILING DATE	GROUP	
	Herewith		

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
TT	1A	4,559,238	12/17/2985	Bujatti, et al.	
TT	1B	5,107,314	04/21/1992	Kahng, et al.	
TT	1C	5,744,864	08/28/1998	Cillessen, et al.	
TT	1D	2003/0047785	02/13/2003	Kawasaki, et al.	
TT	1E	2003/0104659	06/05/2003	Arakawak, et al.	
TT	1F	2003/0111663	06/19/2003	Yagi	
TT	1G	2003/0139026	07/24/2003	Lucovosky	
TT	1H	2003/0180996	09/25/2003	Yamazaki, et al.	
TT	1I	2003/0186489	10/02/2003	Ishikawa	
TT	1J	2003/18221	11/27/2003	Wager, III, et al.	
TT	1K	2003/18222	11/27/2003	Wager, III, et al.	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
TT	1L	WO 97-06544	02/20/1997	Cillessen, et al.		
TT	1M	EP1134811	09/19/2001	Kawasaki, et al.		
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

TT	1Q	Aoki, Akira, et al., "Tin Oxide Thin Film Transistors", Japan J. Appl. Phys., Vol. 9, p.582 (1970).
TT	1R	Carcia, P.F., et al., "Transparent ZnO thin-film transistor fabricated by rf magnetron sputtering", Applied Physics Letters, Vol. 82, No. 7, pp. 1117-1119 (February 17, 2003).
TT	1S	Carcia, P.F., et al., "ZnO Thin Film Transistors for Flexible Electronics", Mat. Res. Soc. Symp. Proc., Vol. 769, pp. H72.1-H72.6 (2003).

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DATE CONSIDERED

10-11-2005

PATENT APPLICATION

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FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

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EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
TT	2A	2003/0224550	12/04/2003	Kokubo, et al.	
TT	2B	60/490,239	07/25/2003		Transparent Thin Film Transistor with Zinc-Tin Oxide Channel...
TT	2C	10/763,239	01/23/2004		Semiconductor Device
TT	2D	10/763,354	01/23/2004		Transistor Including a Deposited Channel Region Having a ...
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	2L					
	2M					
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	2O					
	2P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

TT	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transistion Metal Oxides", SPIE Vol. 2697, pp. 520-527.
TT	2R	Giesbers, J.B., et al., "Dry Etching of All-Oxide Transparent Thin Film Memory Transistors", Microeletronic Engineering, Vol. 35, pp. 71-74 (1997).
TT	2S	Grosse-Holz, K.O., et al. "Semiconductive Behavior of Sb Doped SnO2 Thin Films", Mat. Res. Soc. Symp. Proc., Vol. 401, pp. 67-72 (1996).

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APPLICANT Randy L. Hoffman			
FILING DATE Herewith		GROUP	

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	3L					
	3M					
	3N					
	3O					
	3P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

Π	3Q	Hajnal, Zoltán, et al., "Role of oxygen vacancy defect states in the N-type conduction of B-Ga2O3", Journal of Applied Physics, Vol. 86, No. 7, pp. 3792-3796 (October 1, 1999).
Π	3R	Hajnal, Z., et al., "Theoretical Investigation of the Oxygen Vacancies in B-Ga2O3", Rapid Research Notes, Phys. Stat. Sol. (a), Vol. 171, No. R5 (1999).
Π	3S	Hoffman, R.L., et al., "ZnO-based transparent thin-film transistors", Applied Physics Letters, Vol. 82, No. 5, pp. 733-735 (February 3, 2003).

EXAMINER <div style="text-align: center; font-family: cursive;">Hoffman</div>	DATE CONSIDERED <div style="text-align: center;">10-11-2005</div>
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	4M					
	4N					
	4O					
	4P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

TT	4Q	Masuda, Satoshi, et al., "Transparent thin film transistors using ZnO as an active channel layer and their electrical properties", Journal of Applied Physics, Vol. 93, No. 3, pp. 1624-1630 (February 1, 2003).
TT	4R	Nakano, Yoshitaka, et al. "Electrical properties of thermally oxidized p-GaN metal-oxide-semiconductor diodes", Applied Physics Letters, Vol. 82, No. 15, pp. 2443-2445 (April, 14, 2003).
TT	4S	Nishi, Junya, et al., "High Mobility Thin Film Transistors with Transparent ZnO Channels", Jpn. J. Appl. Phys., Vol. 42, Part 2, No. 4A, pp. L347-L349 (April, 2003).

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PATENT APPLICATION

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FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200315134-1	APPLICATION NO. 10/799,325	CONFIRMATION NO.
APPLICANT Randy L. Hoffman			
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	5L					
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

TT	5Q	Ohya, Yutaka, et al., "Thin Film Transistor of ZnO Fabricated by Chemical Solution Deposition", Jpn. J. Appl. Phys., Vol. 40, Part 1, No. 1, pp. 297-298 (January, 2001).
TT	5R	Orita, Masahiro, et al., "Deep-ultraviolet transparent conductive B-Ga2O3 thin films", Applied Physics Letters, Vol. 77, No. 25, pp. 4166-4168 (December 18, 2002).
TT	5S	Oritia, Masahiro, et al., "Preparation of highly conductive, deep ultraviolet transparent B-Ga2O3 thin film at low deposition temperatures", Thin Solid Films, Vol. 411, pp. 134-139 (2002).

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PATENT APPLICATION

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	200315134-1	10/799,325	
	APPLICANT		
	Randy L. Hoffman		
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	6L					
	6M					
	6N					
	6O					
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

TT	6Q	Pallecchi, Ilaria, et al. "SrTiO ₃ -based metal-insulator-semiconductor heterostructures" Applied Physics Letters, Vol. 78, No. 15, pp. 2244-2246 (April 9, 2001).
TT	6R	Prins, M. W. J., et al., "A ferroelectric transparent thin-film transistor", Applied Physics. Letters, Vol. 68, No. 25, pp. 3650-3652 (June 17, 1996).
TT	6S	Seager, C.H., et al., "Charge Trapping and device behavior in ferroelectric memories", Appl. Phys. Lett., Vol. 68, No. 19, pp. 2660-2662 (May 8, 1996).

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DATE CONSIDERED

10-11-2005

PATENT APPLICATION

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FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200315134-1	APPLICATION NO. 10/799,325	CONFIRMATION NO.
APPLICANT Randy L. Hoffman			
FILING DATE Herewith		GROUP	

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	7L					
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

TT	7Q	Ueda, Naoyuki, et al. "Anistrophy of electrical optical properties in BOGa2O3 single crystals", Appl. Phys. Lett., Vol. 71, No. 7, pp. 933-935 (August 18, 1997).
TT	7R	Ueda, Naoyuki, et al., "Systhesis and control of conductivity of ultraviolet transmitting B-Ga2O3 single crystals", Appl. Phys. Lett., Vol. 70, No. 21, pp. 3561-3563 (June 30, 1997).
TT	7S	Uneno, K., et al. "Field-effect transistor on SrTiO3 with sputtered Al2O3 gate insulator", Applied Physics Letter, Vol. 83, No. 9, pp. 1755-1757 (September 1, 2003).

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PATENT APPLICATION

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FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200315134-1	APPLICATION NO. 10/799,325	CONFIRMATION NO.
APPLICANT Randy L. Hoffman			
FILING DATE Herewith		GROUP	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

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	8L					
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	8Q	Vil lora, E.G., et al., "Infrared Reflectance and Electrical Conductivity of B-Ga2O3", Phys..Stat..Sol. (a), Vo. 193, No. 1, pp. 187-195 (2002).
TT	8R	Wöllensteien, Jürgen, et al., "An insulated gate thin-film transistor using SnO2 as semiconducting channel, a possible new gas sensor device" The 11th European Conference on Solid State Transducers, pp. 471-474 (September 21-24, 1997).
TT	8S	Yoshida, A., "Three Terminal Field Effect Superconducting Device Using SrTiO3 Channel" IEEE Transactions on Applied Superconductivity, Vol. 5, No. 2, pp. 2892-2895 (June, 1995).

EXAMINER 	DATE CONSIDERED 10-11-2005
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PATENT APPLICATION

Sheet 9 of 9

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 2003151341-1	APPLICATION NO. 10/799,325	CONFIRMATION NO.
APPLICANT Randy L. Hoffman			
FILING DATE Herewith		GROUP	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
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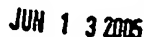
FOREIGN PATENT DOCUMENTS

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	9L					
	9M					
	9N					
	9O					
	9P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

II	9Q	Solid-State Electronics, Vol. 7, Pergamon Press, Notes pp. 701-702 (1964).
II	9R	Anonymous, "Transparent and/or memory thin film transistors in LCD's and PLEAD_" Research Disclosure, p. 890 (July 1998).
	9S	

EXAMINER <div style="text-align: center; font-family: cursive; font-size: 1.2em;">Thoren [Signature]</div>	DATE CONSIDERED <div style="text-align: center;">10-11-2005</div>
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Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449/PTO

(Use as many sheets as necessary)

Sheet	1	of	2
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Complete if Known

Application Number	10/799325
Filing Date	Mar 12, 2004
First Named Inventor	Randy Hoffman
Art Unit	2811
Examiner Name	Thien Tran
Attorney Docket Number	200315134-1

U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ² -Number ⁴ -Kind Code ³ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
		WO 02/15233	02-21-2002	Walter	
		EP 1 306 858	05-02-2003	Japan Science	
		EP 1 367 657	12-03-2003	Koha Co.	

Examiner Signature	<i>[Signature]</i>	Date Considered	10-11-2005
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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